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epitex

PD1450T-35D54-I

Stem Type Photo-Diode

Outline and Internal Circuit



(Unit : mm)

Features

- Non-hermetic package
- Chip Material : InGaAs
- Chip Dimension : 380um * 380um
- Number of Chips : 1pce
- Stem: TO-18 type
- Lens : Flat Glass
- Cap : Gold Plated

Application

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Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Ratings	Unit
Reverse Breakdown Voltage	V(VR)R	20	V
Operating Temperature	Topr	-40 ~ +100	°C
Storage Temperature	Tstg	-40 ~ +100	°C

‡Pulse Forward Current condition : Duty 1% and Pulse Width=10us.

‡Soldering condition : Refer to technical support information on the website.

Optical and Electrical Characteristics (Tc=25°C)

(*: 100% testing, **: reference value)

Parameter	Symbol	Min	Тур	Мах	Unit	Test Condition	
Photo Responsivity	RE		0.95		A/W		λp=1300nm**
			1.00			VR-3V	λp=1550nm**
Photo Current	IL		18		uA	VR=0V λp=1450nm*	
Dark Current	ID			1	nA	VR=5V*	
Spectral Responsivity (Peak)	λρ		1450		nm	VR=0V**	
Half Angle of Sensitivity	θ1/2		±40		deg.	VR=0V**	
Total Capacitance	Ст		4.5		pF	VR=5V f=1MHz **	

‡ Measured by USHIO's calibrated tool.

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Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements. Product data and parameters may vary by user application and over time.

Products shown in this catalog are intended to be used for general electronic equipment. Products are not guaranteed for applications where product malfunction or failure may cause personal injury or death, including but not limited to life-supporting / saving devices, medical devices, safety devices, airplanes, aerospace equipment, automobiles, traffic control systems, and nuclear reactor control systems.

Technical Support Information

https://www.ushio.co.jp/en/led/technology/index.html



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